

Product features

High precision machining technology
Low temperature drift, high power.
Ceramic substrate, 50 Ω coplanar waveguide
Gold wire bonding

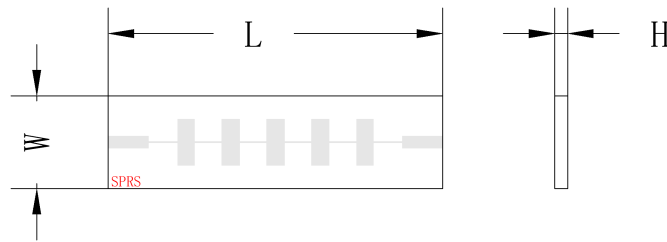
Tech specifications

Items	Parameters	Units
Center Frequency	8.7	GHz
Bandwidth	DC-17.4	GHz
Passband IL	1.5	dB
Ripple	1.5	dB
VSWR	1.7:1	
Group delay ripple	0.4	ns
Rejection	40@21.6-38.0GHz	dBc

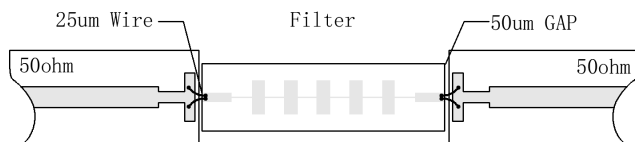
Other requirement (Design assurance)

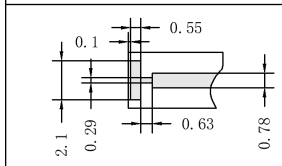
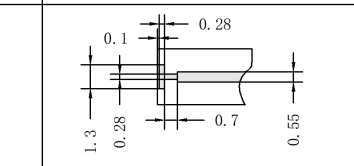
power	1W CW
Work Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:8.5, W:2.5, h:0.26

Outline drawing: Port centered



Suggested PCB Layout

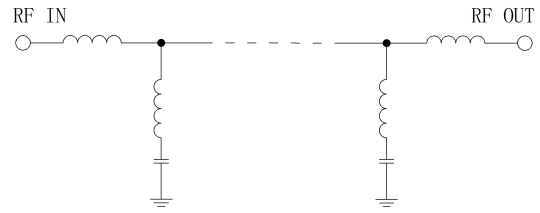


PCB Rogers5880, h:0.254mm	PCB Rogers4350B, h:0.254mm
	

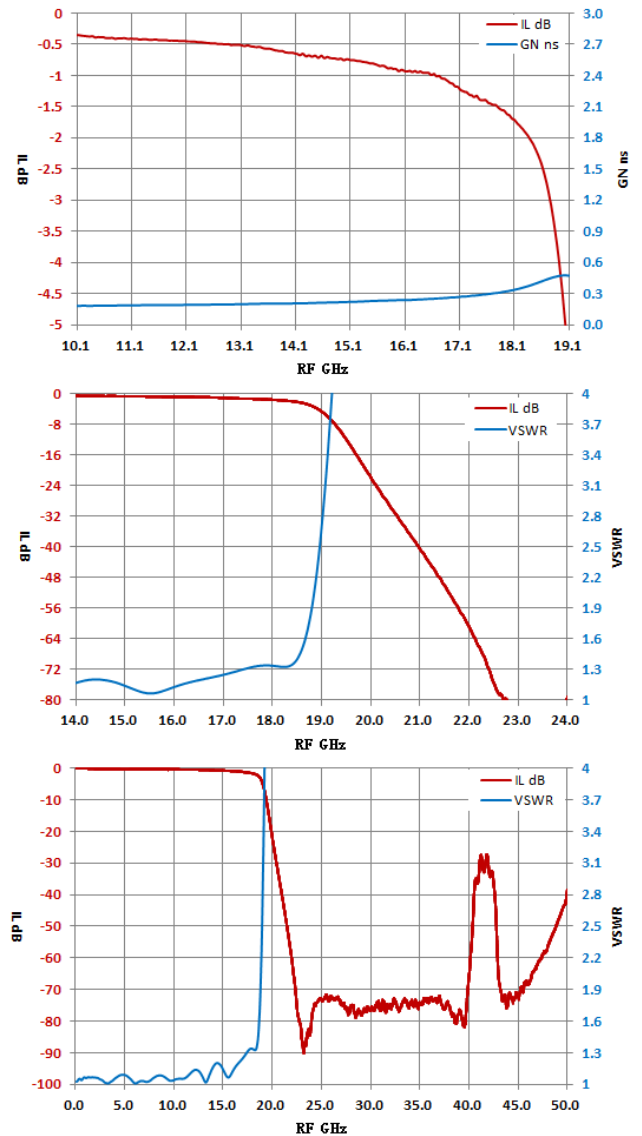
Note

- 0.1mm from the side wall, 1.75mm from the surface to the upper cover.
- Suggest using conductive adhesive for bonding;
- The chip should be installed on kovar alloy or molybdenum copper;
- Suggest using a T-shaped structure for microstrip bonding.

Schematic diagram



Typical test curve



Note: The specifications and performance data contained in this data sheet are based on tests established by COM-MW.